

Fast switching diode chip in EMCON 3-Technology

FEATURES:

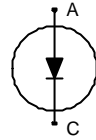
- 600V EMCON 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power module
- discrete components

Applications:

- drives
- white goods
- resonant applications



| Chip Type | V _R | I _F | Die Size | Package |
|-------------|----------------|----------------|-----------------------------|--------------|
| SIDC06D60C6 | 600V | 20A | 2.34 x 2.42 mm ² | sawn on foil |

MECHANICAL PARAMETER:

| | | |
|---------------------------------|--|-----------------|
| Raster size | 2.34 x 2.42 | mm ² |
| Area total / active | 5.66 / 3.85 | |
| Anode pad size | 1.92 x 2 | |
| Thickness | 70 | µm |
| Wafer size | 150 | mm |
| Flat position | 180 | deg |
| Max. possible chips per wafer | 2581 pcs | |
| Passivation frontside | Photoimide | |
| Anode metallization | 3200 nm AlSiCu | |
| Cathode metallization | Ni Ag –system suitable for epoxy and soft solder die bonding | |
| Die bond | electrically conductive glue or solder | |
| Wire bond | Al, ≤500µm | |
| Reject ink dot size | Ø 0.65mm; max 1.2mm | |
| Recommended storage environment | store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C | |

Maximum Ratings

| Parameter | Symbol | Condition | Value | Unit |
|--|----------------|-----------|------------|------|
| Repetitive peak reverse voltage | V_{RRM} | | 600 | V |
| Continuous forward current limited by T_{jmax} | I_F | | 1) | A |
| Maximum repetitive forward current limited by T_{jmax} | I_{FRM} | | 40 | |
| Operating junction and storage temperature | T_j, T_{stg} | | -40...+175 | °C |

1) depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | | Value | | | Unit |
|---------------------------------|----------|--------------|--------------------|-------|------|------|------|
| | | | | min. | Typ. | max. | |
| Reverse leakage current | I_R | $V_R=600V$ | $T_j=25\text{ °C}$ | | | 27 | µA |
| Cathode-Anode breakdown Voltage | V_{Br} | $I_R=0.25mA$ | $T_j=25\text{ °C}$ | 600 | | | V |
| Forward voltage drop | V_F | $I_F=20A$ | $T_j=25\text{ °C}$ | 1.25 | 1.6 | 1.95 | V |

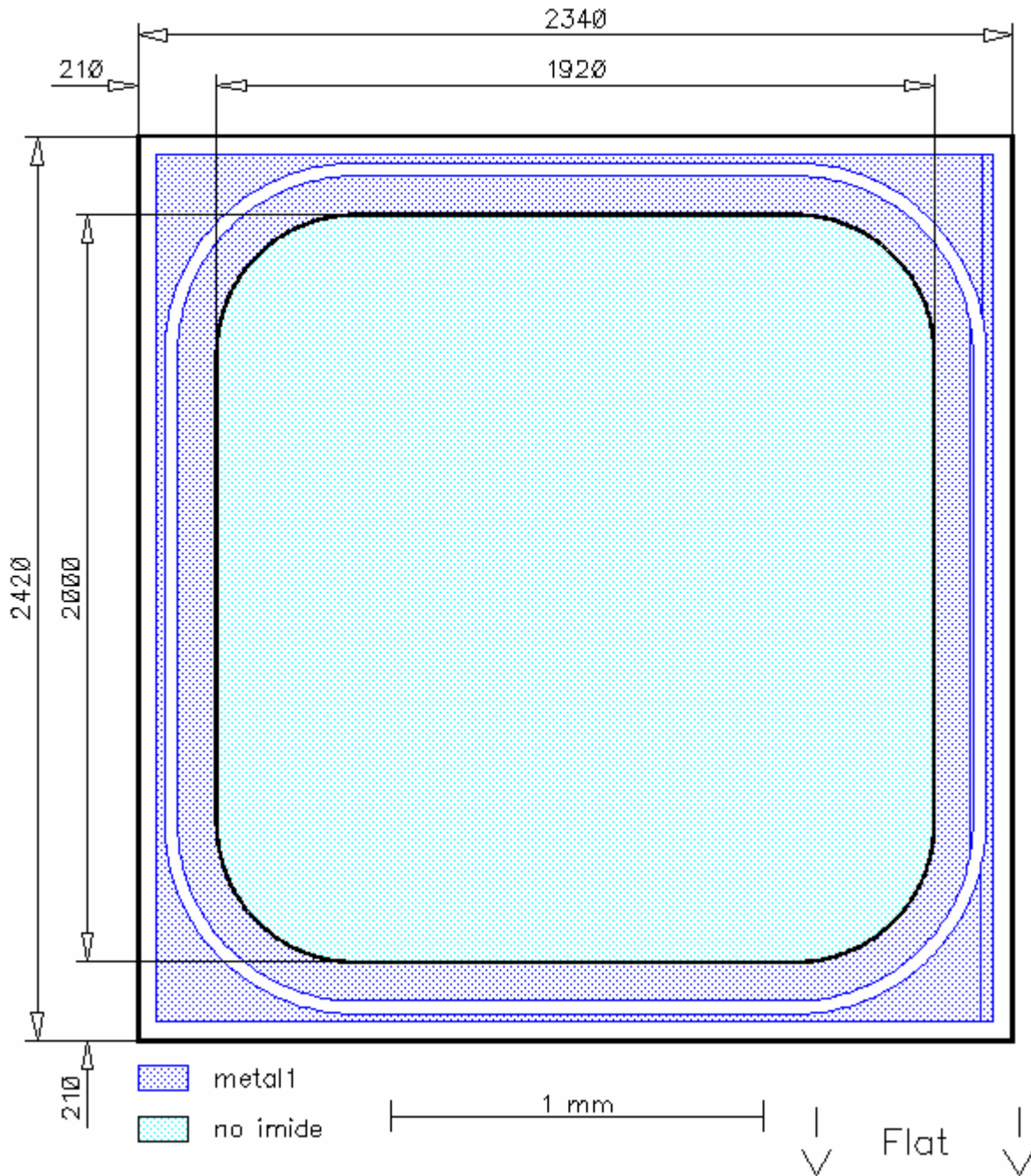
Dynamic Electrical Characteristics (verified by design/characterization), inductive load

| Parameter | Symbol | Conditions | | Value ²⁾ | | | Unit |
|-------------------------------|-----------|--|--|---------------------|----------------------|------|------|
| | | | | min. | Typ. | max. | |
| Peak reverse recovery current | I_{RM} | $I_F=20A$ $di/dt=1800A/ms$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ $T_j = 150\text{ °C}$ | | 30.0 32.0 34.0 | | A |
| Recovered charge | Q_r | $I_F=20A$ $di/dt=1800A/ms$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ $T_j = 150\text{ °C}$ | | 1.00 1.75 2.20 | | µC |
| Reverse recovery energy | E_{rec} | $I_F=20A$ $di/dt=1800A/ms$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ $T_j = 150\text{ °C}$ | | 0.21 0.37 0.47 | | mJ |

²⁾ values also influenced by parasitic L- and C- in measurement and package.

CHIP DRAWING:

Die-Size 2340 um x 2420 um
 20A Modul , active area 3,85mm²





SIDC06D60C6

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the
device data sheet

FS20R06VE3

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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